

propylene glycol; and

citric acid acting as a surface passivation agent, wherein

said conditioning solution is substantially non-aqueous.

145. (Amended) The solution of claim 144, wherein said solution comprises approximately 0.01 to approximately 5.0 percent hydrofluoric acid, approximately 1 to approximately 15 percent phosphoric acid, approximately 80 to approximately 90 percent propylene glycol, and approximately 0.001 to approximately 1.0 percent citric acid.

150. (Amended) A conditioning solution for use in removing residues remaining on a semiconductor substrate after a dry etch process, said conditioning solution comprising:

hydrofluoric acid;

hydrochloric acid;

propylene glycol; and

citric acid acting as a surface passivation agent, wherein

said conditioning solution is substantially non-aqueous.

155. (Amended) The solution of claim 154, wherein said solution comprises approximately 0.25 to approximately 0.3 percent hydrofluoric acid, approximately 0.005 to approximately 0.009 percent hydrochloric acid, approximately 90 to approximately 98 percent propylene glycol, and approximately 0.009 to approximately 0.5 percent citric acid.

Sub 3 158. (Amended) A conditioning solution for use in removing residues remaining on a semiconductor substrate after a dry etch process consisting essentially of a fluorine source, a complementary acid, a non-aqueous solvent and a surface passivation agent, wherein
DP said conditioning solution is substantially non-aqueous.

159. (Amended) The solution of claim 158, wherein the fluorine source is hydrofluoric acid, the complementary acid is phosphoric acid, the non-aqueous solvent is propylene glycol and the surface passivation agent is citric acid.

160. (Amended) The solution of claim 158, wherein the fluorine source is hydrofluoric acid, the complementary acid is hydrochloric acid, the non-aqueous solvent is propylene glycol and the surface passivation agent is citric acid.